SIDC16D60SIC3

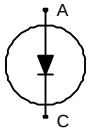
Silicon Carbide Schottky Diode

FEATURES:

- Worlds first 600V Schottky diode
- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- Ideal diode for Power Factor Correction
- No forward recovery

Applications:

- SMPS, PFC, snubber



Chip Type	V_{BR}	I_F	Die Size	Package	Ordering Code
SIDC16D60SIC3	600V	5A	1.26 x 1.26 mm^2	sawn on foil	Q67050-A4271-A101

MECHANICAL PARAMETER:

Raster size	1.26 x 1.26	mm
Anode pad size	0.960 x 0.960	
Area total / active	1.588 / 0.96	mm^2
Thickness	355	µm
Wafer size	75	mm
Flat position	0	deg
Max. possible chips per wafer	2457 pcs	
Passivation frontside	Photoimide	
Anode metalization	3200 nm Al	
Cathode metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤ 125µm	
Reject Ink Dot Size	∅ ≥ 0.2 mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Surge peak reverse voltage	V_{RSM}		600	
Continuous forward current limited by T_{jmax}	I_F		5	A
Single pulse forward current (depending on wire bond configuration)	I_{FSM}	T_C =25°C, t_P =10 ms sinusoidal	18.5	
Maximum repetitive forward current limited by T_{jmax}	I_{FRM}	T_C = 100°C, T_j=150°C, D=0.1	21	
Non repetitive peak forward current	I_{FMAX}	T_C =25°C, tp=10µs	50	
Operating junction and storage temperature	T_j , T_{stg}		-55...+175	°C

Static Electrical Characteristics (tested on chip), T_j=25 °C, unless otherwise specified

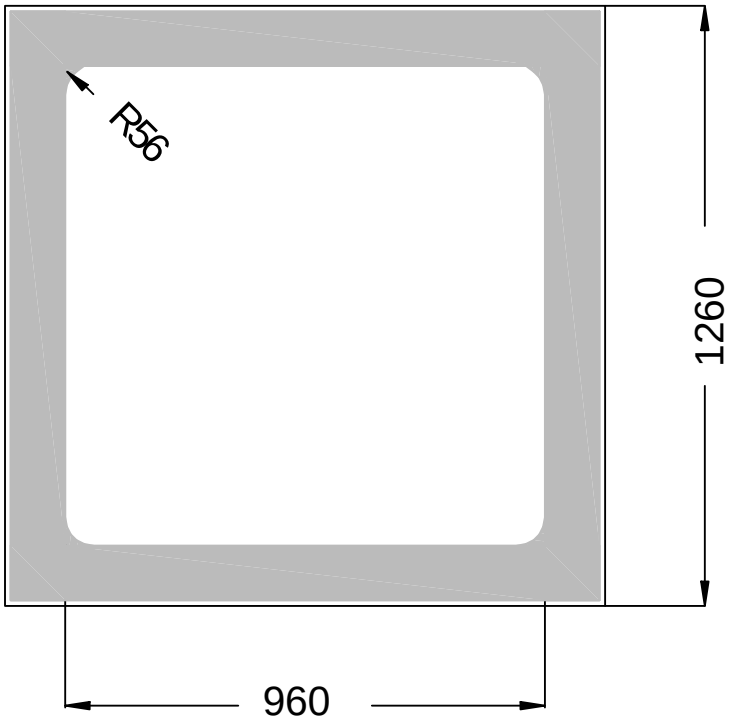
Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse leakage current	I_R	V_R=600V*	T_j=25°C		19	200	µA
Forward voltage drop	V_F	I_F=5A	T_j=25°C		1.5	1.7	V

* blocking characteristic measured under protective gas atmosphere. Chip should not be used without being embedded in pottant with breakdown field strength lower than 9 KV/mm at full blocking voltage.

Dynamic Electrical Characteristics, at T_j = 25 °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Total capacitive charge	Q_C	I_F=5A di/dt=200A/ms V_R=400V	T_j = 150 °C		14		nC
Switching time	t_{rr}	I_F=5A di/dt=200A/ms V_R= 400V	T_j = 150 °C		n.a.		ns
Total capacitance	C	I_F=5A di/dt=200A/ms T_j=25°C f=1MHz	V_R=1V		170		pF
			V_R=300V		16		
			V_R=600V		12		

CHIP DRAWING:



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FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	INFINEON TECHNOLOGIES	SDT05S60

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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